

CMESDF08V2R5C4R5DFE is a low-capacitance Transient Voltage Suppressor (TVS) array designed to provide electrostatic discharge (ESD) protection for high-speed data interfaces. With typical capacitance of

4.5pF only, CMESDF08V2R5C4R5DFE is designed to

over-voltage and over-current transient events. It complies with IEC 61000-4-2 (ESD), Level 4 (±15kV air, ±8kV contact discharge), IEC 61000-4-4 (electrical

fast transient - EFT) (40A, 5/50 ns), IEC 61000-4-5 (Surge) (10A,8/20µs), very fast charged device model (CDM) ESD and cable discharge event (CDE), etc.

robustness make CMESDF08V2R5C4R5DFE ideal

for high-speed data port and high-frequency line (e.g., Gigabit Ethernet Ports) applications. The low clamping voltage of the CMESDF08V2R5C4R5DFE guarantees

CMESDF08V2R5C4R5DFE is in a DFN-8L package. Each CMESDF08V2R5C4R5DFE device can protect two high-speed line pairs. The "flow-thru" design minimizes trace inductance and reduces voltage overshoot associated with ESD events. The combined features of low capacitance and high ESD

systems

against

parasitic-sensitive

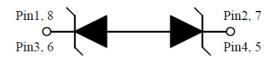
DESCRIPTIONS

protect

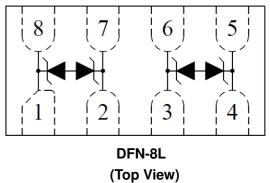
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Low Capacitance ESD/Surge Protection for Gigabit Ethernet Interfaces

Circuit Diagram



Pin Configuration



FEATURES

1. Transient protection for high-speed data lines IEC 61000-4-2 (ESD) ±30kV (Air)

±30kV (Contact)

IEC 61000-4-4 (EFT) 40A (5/50 ns) IEC 61000-4-5 (Surge) 10A (8/20µs)

a minimum stress on the protected IC.

- 2. Package optimized for high-speed lines
- 3. Provides protection for two line pairs
- 4. Low capacitance: 4.5pF @ 2.5V (Typical)
- 5. Low leakage current: 10nA @ V_{RWM} (Typical)
- 6. Low operating and clamping voltage
- 7. Each I/O pin can withstand over 1000 ESD strikes for ±8kV contact discharge

Applications

- 1, 10/100/1000M Ethernet Ports
- 2、WAN/LAN Equipment
- 3. Desktops, Servers and Notebooks
- 4. Cellular Phones
- 5. Switching Systems
- 6. Audio/Video Inputs

Mechanical Characteristics

- 1. DFN-8L package
- 2. Flammability Rating: UL 94V-0
- 3. Marking: Part number, Date
- 4. Packaging: Tape and Reel

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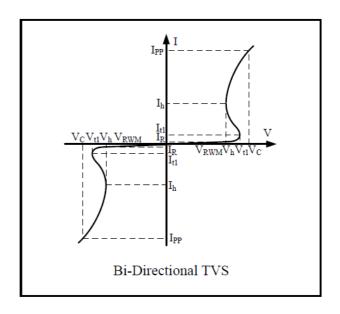
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◆ Absolute Maximum Rating

Symbol	Parameter	Value	Units	
I _{PP}	Peak Pulse Current (8/20µs)	10	Α	
P_{PK}	Peak Pulse Power (8/20µs)	100	W	
V _{ESD}	ESD per IEC 61000-4-2 (Air)	±30	kV	
	ESD per IEC 61000-4-2 (Contact)	±30		
T_OPT	Operating Temperature	-45/+85	${\mathbb C}$	
T _{STG}	Storage Temperature	-55/+150	$^{\circ}$	

◆ Electrical Characteristics (T = 25°C)

Symbol	Parameter		
I _R	Reverse Leakage Current @ V _{RWM}		
V _{t1}	Trigger Voltage		
I _{t1}	Trigger Current @ V _{t1}		
V_h	Holding Voltage		
I _h	Holding Current @ V _h		
V _C	Clamping Voltage @ I _{PP}		
I _{PP}	Maximum Peak Pulse Current		
V_{F}	Forward Voltage @ I _F		
C _{ESD}	Parasitic Capacitance		
C_{Δ}	Variation in C _{ESD} with Reverse Bias		



Symbol	Test Condition	Minimum	Typical	Maximum	Units
V_{RWM}		-	-	2.5	V
I _R	V_{RWM} = 2.5V, T = 25 $^{\circ}$ C		10	50	nA
V_{t1}	$I_{t1} = 1\mu A$	3.0	3.7	4.5	V
V_h	$I_h = 1mA$	3.0		4.0	V
V _C	I_{PP} = 1A, tp = 8/20µs (Each Line)	-	-	5.0	V
V _C	$I_{PP} = 10A$, $tp = 8/20\mu s$ (Each Line)	-	-	8.0	V
V _C	I_{PP} = 25A, tp = 8/20µs (Each Line)	-	-	15.0	V
C _{ESD}	Between I/O Pins and Ground $V_R = 0V$, $f = 1MHz$	-	4.5	6.0	pF
C _{ESD}	Between I/O Pins V _R = 0V, f = 1MHz	-	1.3	-	pF

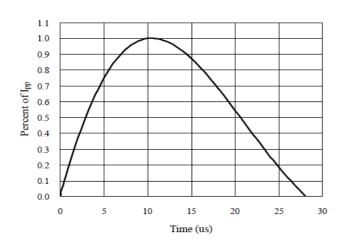
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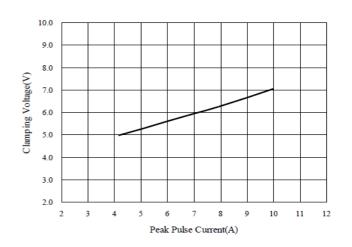
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◆ TYPICAL ELECTRICAL CHARACTERISTICS CURVE

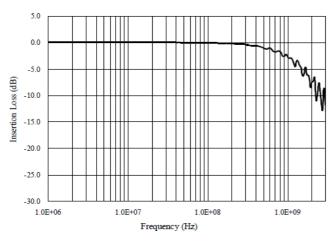
8/20µs Pulse Waveform



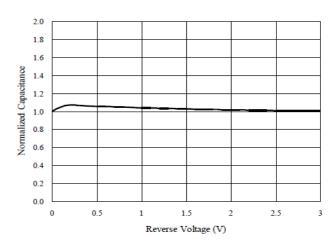
Clamping Voltage V_C vs. Current I_{PP}



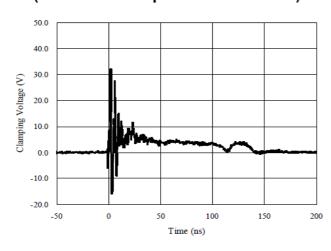
Insertion Loss S21



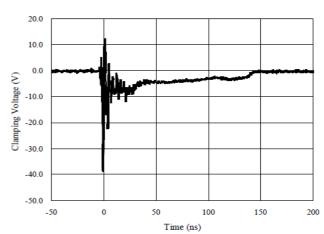
Normalized Capacitance vs. Voltage



ESD Clamping of I/O to GND (+8kV Contact per IEC 61000-4-2)



ESD Clamping of I/O to GND (-8kV Contact per IEC 61000-4-2)

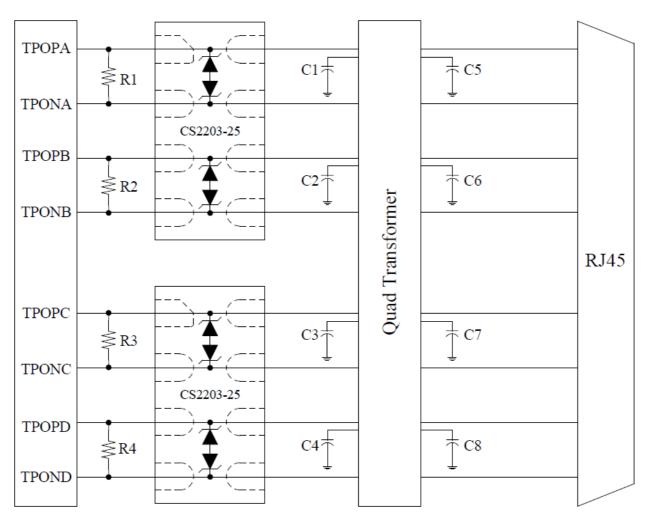


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Application Information

Electronic equipment is susceptible to damage caused by a variety of sources, including Electrostatic Discharge (ESD), Electrical Fast Transients (EFT) and Lightning strikes. The CMESDF08V2R5V4R5DFE was designed to protect the sensitive equipment from damage which may be induced by such transient events. This product can be configured in a connection to meet the requirement of differential line pairs as follows:

♦ Gigabit Ethernet Protection



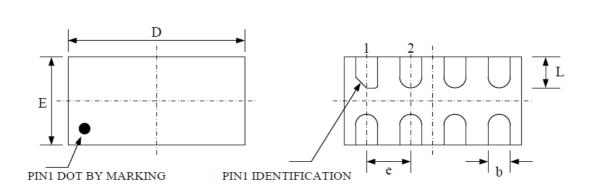
Schematic Diagram for Gigabit Ethernet ESD/Surge Protection

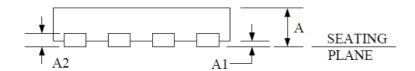
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◆ PACKAGE OUTLINE

- 1、DFN-8L Package
- 2、Flow-Through
- 3、MSL 1 & Thermally-Enhanced





Package Dimensions (Controlling dimensions are in millimeters)

Symbol	Dimensions (mm)		Dimensions (Inches)			
	Minimum	Typical	Maximum	Minimum	Typical	Maximum
A	0.370	0.400	0.430	0.015	0.016	0.017
A1	0.000	0.020	0.050	0.000	0.001	0.002
A2	0.130			0.005		
ь	0.200	0.250	0.300	0.008	0.010	0.012
D	1.900	2.000	2.100	0.075	0.079	0.083
E	0.900	1.000	1.100	0.035	0.039	0.043
e	0.500 BSC			0.020 BSC		
L	0.300	0.350	0.400	0.012	0.014	0.016
R	0.050	0.100	0.150	0.002	0.004	0.006

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